Abstracts

Broadband High-Efficiency MMIC Power Amplifiers Using Ion-Implanted MESFET Technology

Y.C. Shih, K. Tan, K. Kasel, K.K. Yu and S.K. Wang. "Broadband High-Efficiency MMIC Power Amplifiers Using Ion-Implanted MESFET Technology." 1989 MTT-S International Microwave Symposium Digest 89.3 (1989 Vol. III [MWSYM]): 1119-1120.

Broadband high-efficiency MMIC amplifiers had been designed and fabricated using ion-implanted MESFET technology. In the 7.5 to 18 GHz bandwidth, the amplifier has demonstrated a power-added efficiency of 15 to 34 percent, averaging greater than 20 percent. The output power is about 24 dBm at 1-dB compression and 26 dBm at 2-dB compression.

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